# 2SB0939 (2SB939), 2SB0939A (2SB939A)

Silicon PNP epitaxial planar type Darlington

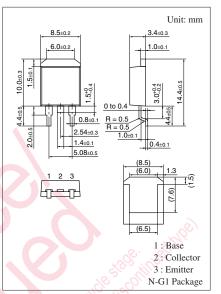
For midium-speed power switching Complementary to 2SD1262, 2SD1262A

#### Features

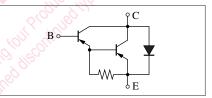
- $\bullet$  High forward current transfer ratio  $h_{F\!E}$
- High-speed switching
- N type package enabling direct soldering of the radiating fin to the printed circuit board, etc. of small electronic equipment.

Parameter	Symbol	Rating	Unit	
Collector-base voltage	2SB0939	V <sub>CBO</sub>	-60	V
(Emitter open)	2SB0939A		-80	
Collector-emitter voltage	2SB0939	V <sub>CEO</sub>	-60	V
(Base open)	2SB0939A		-80	
Emitter-base voltage (Coll	V <sub>EBO</sub>	-7	V	
Collector current	I <sub>C</sub>	-8	А	
Peak collector current	I <sub>CP</sub>	-12	А	
Collector power dissipation		P <sub>C</sub>	45	W
	$T_a = 25^{\circ}C$		1.3	
Junction temperature		Tj	150	°C
Storage temperature		T <sub>stg</sub>	-55 to +150	°C

#### Absolute Maximum Ratings $T_C = 25^{\circ}C$



Note) Self-supported type package is also prepared. Internal Connection



#### Electrical Characteristics $T_C = 25^{\circ}C \pm 3^{\circ}C$

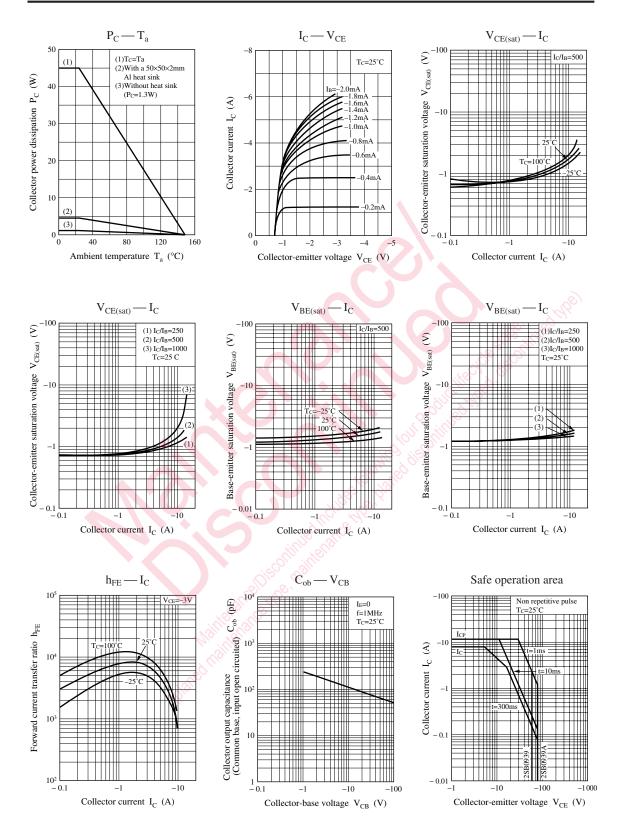
Parameter		Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage	2SB0939	V <sub>CEO</sub>	$I_{\rm C} = -30$ mA, $I_{\rm B} = 0$	-60			V
(Base open)	2SB0939A		onthin terr	-80			
Collector-base cut-off	2SB0939	I <sub>CBO</sub>	$V_{CB} = -60 \text{ V}, I_E = 0$			-100	μΑ
current (Emitter open)	2SB0939A	200	$V_{CB} = -80 \text{ V}, I_E = 0$			-100	
Emitter-base cutoff current (Co	llector open)	I <sub>EBO</sub>	$V_{\rm EB} = -7 \text{ V}, I_{\rm C} = 0$			-2	mA
Forward current transfer rat	io	h <sub>FE1</sub> *	$V_{CE} = -3 V, I_C = -4 A$	2000		10000	
		h <sub>FE2</sub>	$V_{CE} = -3 V, I_C = -8 A$	500			
Base-emitter saturation volt	age	V <sub>BE(sat)</sub>	$I_{\rm C} = -4 \text{ A}, I_{\rm B} = -8 \text{ mA}$			-2	V
Collector-emitter saturation	voltage	V <sub>CE(sat)</sub>	$I_{C} = -4 A, I_{B} = -8 mA$			-1.5	V
Transition frequency	C.	f <sub>T</sub>	$V_{CE} = -10 \text{ V}, I_C = -0.5 \text{ A}, f = 1 \text{ MHz}$		20		MHz
Turn-on time		t <sub>on</sub>	$I_{\rm C} = -4$ A,		0.5		μs
Strage time		t <sub>stg</sub>	$I_{B1} = -8 \text{ mA}, I_{B2} = 8 \text{ mA}$		2		μs
Fall time		t <sub>f</sub>	$V_{\rm CC} = -50  {\rm V}$		1		μs

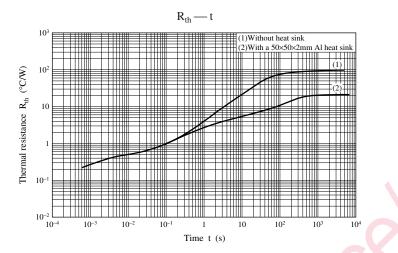
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors. 2. \*: Rank classification

Rank	Q	Р
$h_{\rm FE1}$	2000 to 5000	4000 to 10000

Note) The part number in the parenthesis shows conventional part number.

### Panasonic





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